

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (U-MOS II)

2SK2987

HIGH CURRENT SWITCHING APPLICATIONS

DC-DC CONVERTER, RELAY DRIVE AND MOTOR DRIVE APPLICATIONS

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 4.5m\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 80S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 60V$)
- Enhancement-Mode : $V_{th} = 1.3 \sim 2.5V$ ($V_{DS} = 10V$, $I_D = 1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	70	A
	Pulse	I_{DP}	280	
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	150	W
Single Pulse Avalanche Energy**		E_{AS}	490	mJ
Avalanche Current		I_{AR}	70	A
Repetitive Avalanche Energy*		E_{AR}	15	mJ
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	0.833	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	50	$^\circ C/W$

Note ;

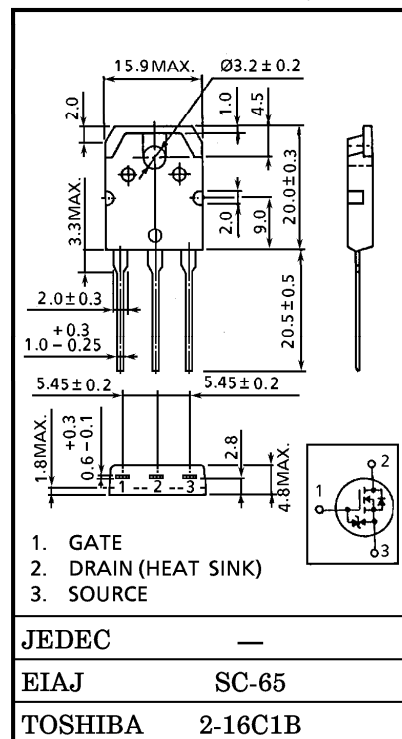
* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 25V$, Starting $T_{ch} = 25^\circ C$, $L = 136\mu H$, $I_{AR} = 70A$, $R_G = 25\Omega$

This transistor is an electrostatic sensitive device.
Please handle with caution.

INDUSTRIAL APPLICATIONS

Unit in mm

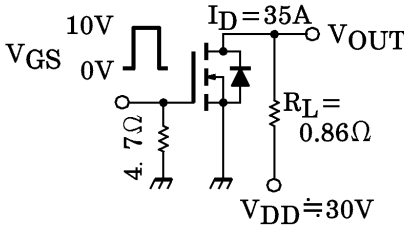


Weight 4.6g

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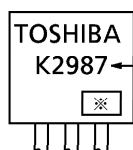
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I _{GSS}	V _{GS} =±16V, V _{DS} =0V	—	—	±10	μA
Drain Cut-off Current		I _{DSS}	V _{DS} =60V, V _{GS} =0V	—	—	100	μA
Drain-Source Breakdown Voltage	V _(BR) DSS	I _D =10mA, V _{GS} =0V	60	—	—	V	
	V _(BR) DSX	I _D =10mA, V _{GS} =−20V	40	—	—		
Gate Threshold Voltage		V _{th}	V _{DS} =10V, I _D =1mA	1.3	—	2.5	V
Drain-Source ON Resistance		R _{DS} (ON)	V _{GS} =10V, I _D =35A	—	4.5	5.8	mΩ
			V _{GS} =4V, I _D =35A	—	5.8	10	
Forward Transfer Admittance		Y _{fs}	V _{DS} =10V, I _D =35A	40	80	—	S
Input Capacitance		C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz	—	9300	—	pF
Reverse Transfer Capacitance		C _{rss}		—	910	—	
Output Capacitance		C _{oss}		—	1435	—	
Switching Time	Rise Time	t _r		—	18	—	ns
	Turn-on Time	t _{on}		—	50	—	
	Fall Time	t _f		—	110	—	
	Turn-off Time	t _{off}		V _{IN} : t _r , t _f <5ns Duty ≤1%, t _w =10μs	—	480	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q _g	V _{DD} ≐48V, V _{GS} =10V, I _D =70A	—	210	—	nC
Gate-Source Charge		Q _{gs}		—	145	—	
Gate-Drain (“Miller”) Charge		Q _{gd}		—	65	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	70	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	280	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 70A, V_{GS} = 0V$	—	—	-1.5	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 70A, V_{GS} = 0V$	—	60	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 50A / \mu s$	—	50	—	nC

MARKING



TYPE

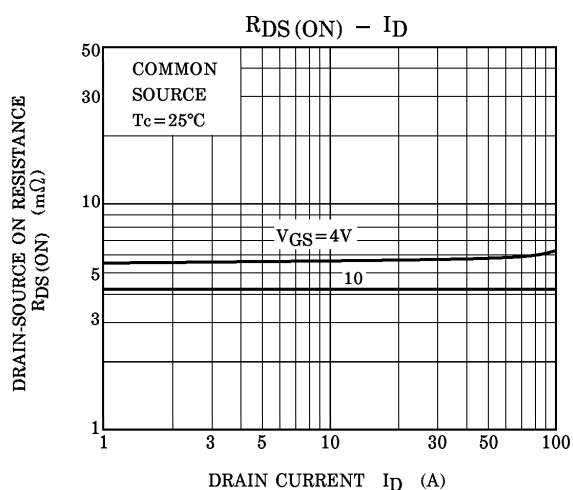
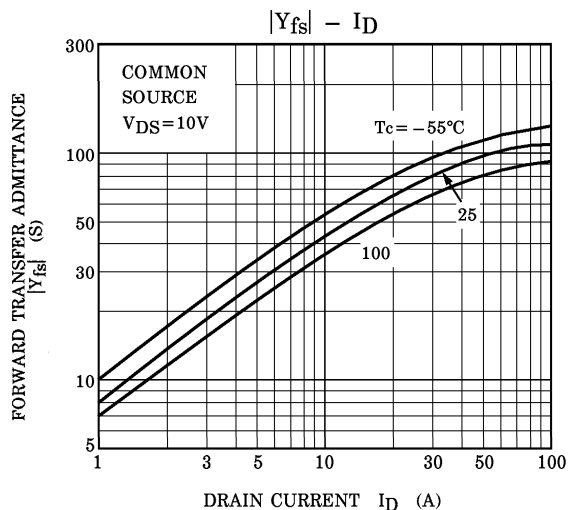
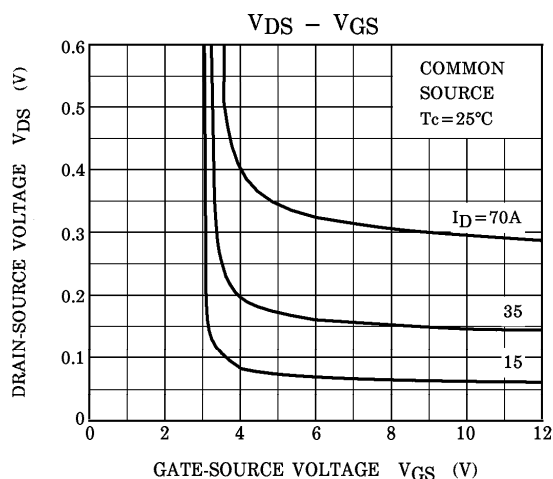
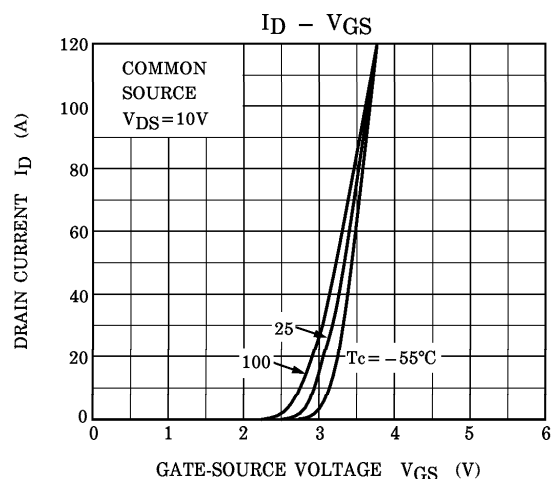
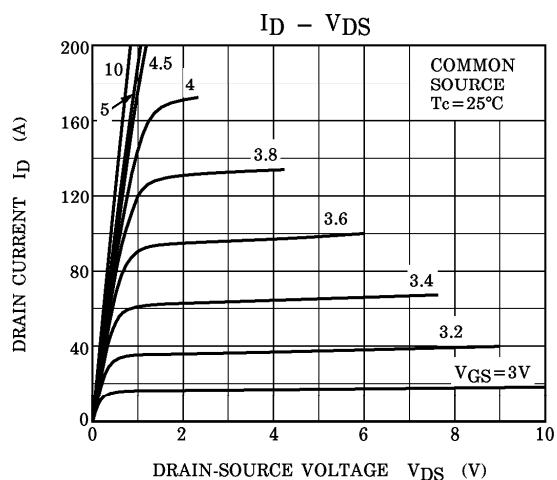
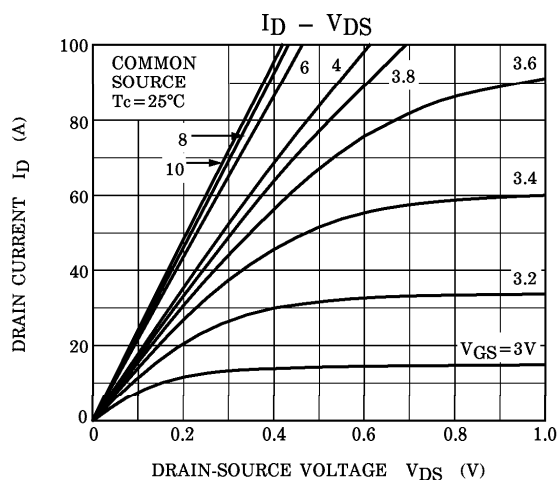
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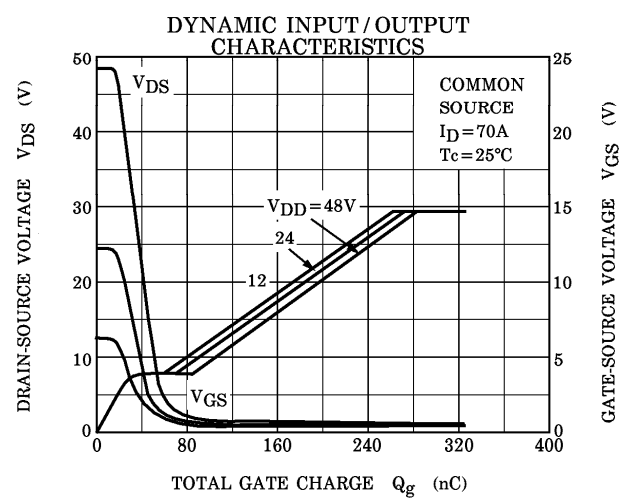
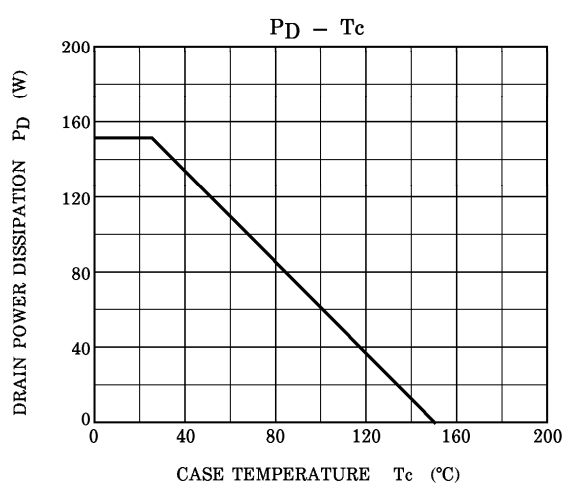
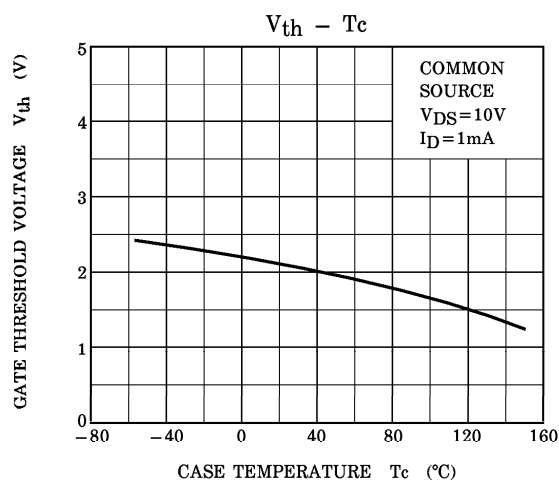
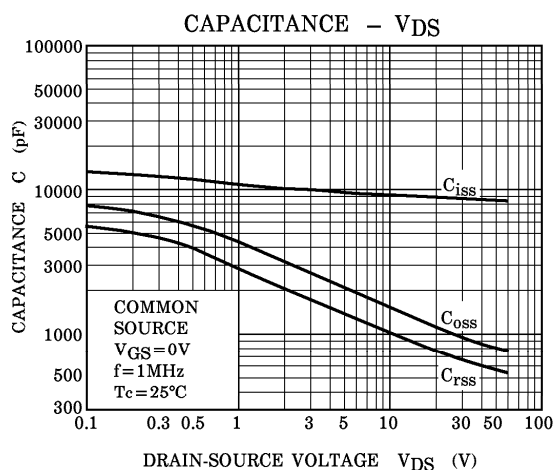
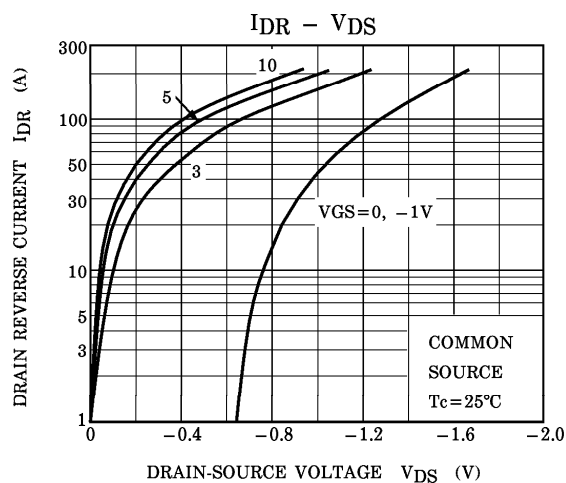
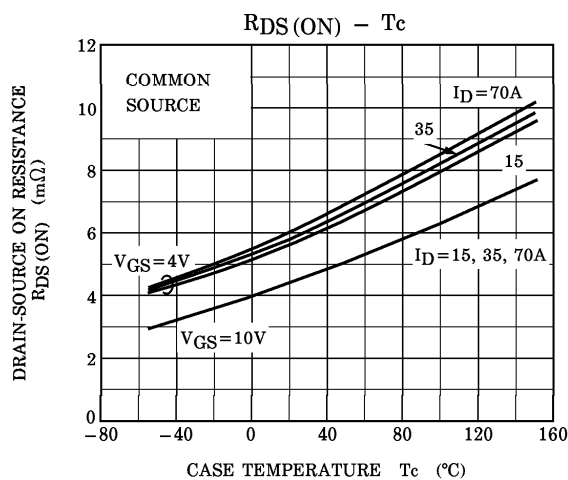


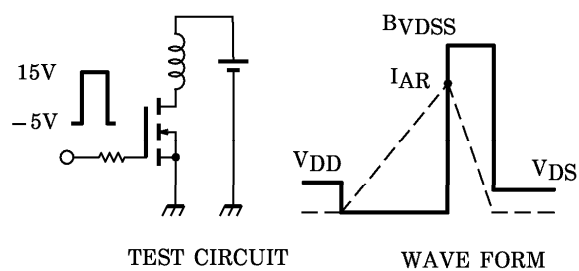
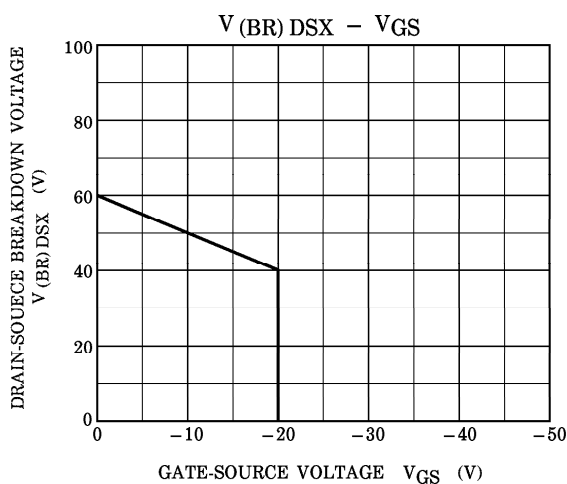
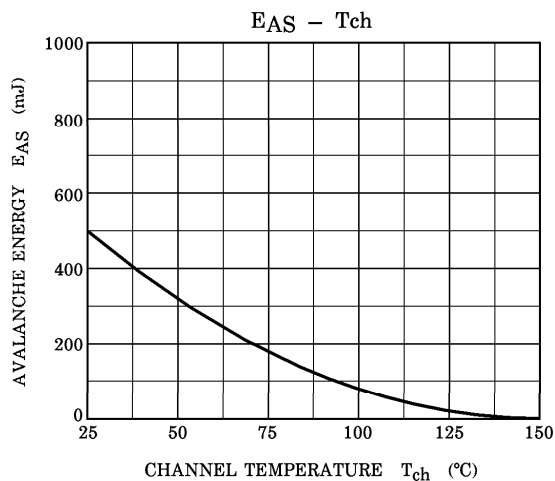
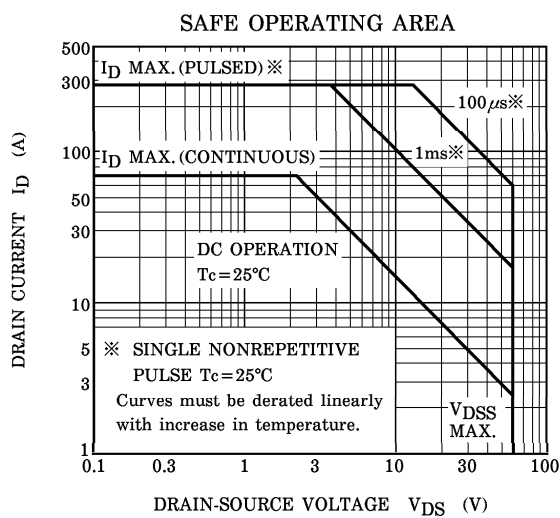
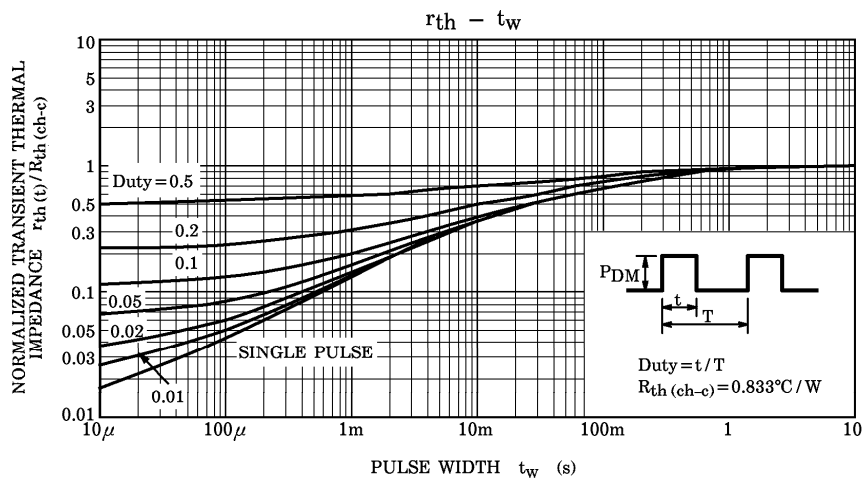
Month (Starting from Alphabet A)



Year (Last Number of the Christian Era)







Peak $I_{AR} = 70A$, $R_G = 25\Omega$
 $V_{DD} = 25V$, $L = 136\mu H$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$